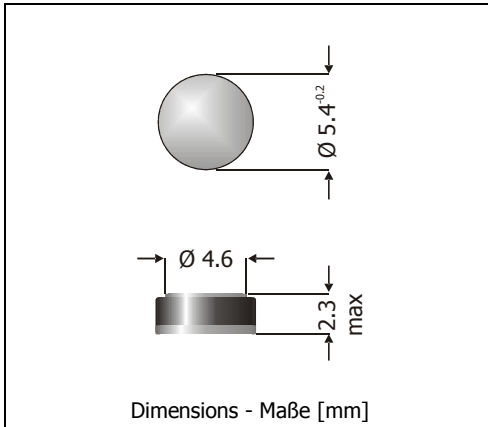


## AG3A ... AG3M

### Silicon Rectifier Cells with Polysiloxane Cover Silizium-Gleichrichterzellen mit Polysiloxan-Abdeckung

Version 2012-02-06

Nominal current 3 A

Nennstrom

Repetitive peak reverse voltage 50...1000 V

Periodische Spitzensperrspannung

Weight approx. – Gewicht ca. 0.3 g

Standard packaging bulk

Standard Lieferform lose



#### Maximum ratings

#### Grenzwerte

| Type<br>Typ | Repetitive peak reverse voltage<br>Periodische Spitzensperrspannung<br>$V_{RRM}$ [V] | Surge peak reverse voltage<br>Stoßspitzensperrspannung<br>$V_{RSM}$ [V] |
|-------------|--|---|
| AG3A        | 50   | 80  |
| AG3B        | 100  | 130   |
| AG3D        | 200  | 250   |
| AG3G        | 400  | 450   |
| AG3J        | 600  | 700   |
| AG3K        | 800  | 1000  |
| AG3M        | 1000   | 1300  |

|   |                           |                |                              |
|---|---------------------------|----------------|------------------------------|
| Max. average forward rectified current, R-load<br>Dauergrenzstrom in Einwegschaltung mit R-Last     | $T_T = 100^\circ\text{C}$ | $I_{FAV}$      | 3 A                          |
| Repetitive peak forward current<br>Periodischer Spitzenstrom  | $f > 15\text{ Hz}$        | $I_{FRM}$      | 30 A <sup>1)</sup>           |
| Peak forward surge current, 50/60 Hz half sine-wave<br>Stoßstrom für eine 50/60 Hz Sinus-Halbwellen | $T_A = 25^\circ\text{C}$  | $I_{FSM}$      | 150/165 A                    |
| Rating for fusing, $t < 10\text{ ms}$<br>Grenzlastintegral, $t < 10\text{ ms}$                      | $T_A = 25^\circ\text{C}$  | $i^2t$         | 110 A <sup>2</sup> s         |
| Junction temperature – Sperrschichttemperatur<br>Storage temperature – Lagerungstemperatur          |                           | $T_j$<br>$T_s$ | -50...+125°C<br>-50...+150°C |

#### Characteristics

#### Kennwerte

|                                      |   |       |                    |
|--------------------------------------|---|-------|--------------------|
| Forward voltage – Durchlass-Spannung | $T_j = 25^\circ\text{C}$ $I_F = 3\text{ A}$ | $V_F$ | < 1.2 V            |
| Leakage current – Sperrstrom         | $T_j = 25^\circ\text{C}$ $V_R = V_{RRM}$    | $I_R$ | < 10 $\mu\text{A}$ |

1 Max. temperature of the cell  $T = 125^\circ\text{C}$  – Max. Temperatur der Zelle  $T = 125^\circ\text{C}$